

# **Plastic Medium-Power Silicon NPN Darlingtons**

# **BD675G, BD675AG, BD677G**, **BD677AG**, **BD679G, BD679AG, BD681G**

This series of plastic, medium-power silicon NPN Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

#### **Features**

- High DC Current Gain
- Monolithic Construction
- Complementary to BD676, 676A, 678, 678A, 680, 680A, 682
- BD677, 677A, 679, 679A are Equivalent to MJE 800, 801, 802, 803
- These Devices are Pb-Free and are RoHS Compliant\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	V <sub>CEO</sub>	45 60 80 100	Vdc
Collector-Base Voltage BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	V <sub>CBO</sub>	45 60 80 100	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current	I <sub>C</sub>	4.0	Adc
Base Current	Ι <sub>Β</sub>	1.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	40 0.32	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

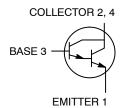
# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.13	°C/W

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

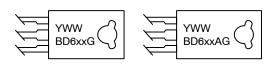
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# 4.0 AMPERES **POWER TRANSISTORS** NPN SILICON 60, 80, 100 VOLTS, 40 WATTS





#### MARKING DIAGRAMS



BD6xx/BD6xxA = Device Code x = 75, 77, 79, 81

= Year ww = Work Week = Pb-Free Package

## **ORDERING INFORMATION**

See detailed ordering and shipping information on page 4 of this data sheet.

NOTE: Some of the devices on this data sheet have been DISCONTINUED. Please refer to the table on page 3.

# BD675G, BD675AG, BD677G, BD677AG, BD679G, BD679AG, BD681G

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•			
Collector-Emitter Breakdown Voltage, (Note 1) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 0) BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	BV <sub>CEO</sub>	45 60 80 100	- - - -	Vdc
Collector Cutoff Current $(V_{CE} = Half Rated V_{CEO}, I_B = 0)$	I <sub>CEO</sub>	-	500	μAdc
Collector Cutoff Current $(V_{CB} = \text{Rated BV}_{CEO}, I_E = 0)$ $(V_{CB} = \text{Rated BV}_{CEO}, I_E = 0, T_C = 100^{\circ}\text{C})$	I <sub>CBO</sub>	<u>-</u>	0.2 2.0	mAdc
Emitter Cutoff Current (V <sub>BE</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	2.0	mAdc
ON CHARACTERISTICS	•			
DC Currert Gain, (Note 1) (I <sub>C</sub> = 1.5 Adc, V <sub>CE</sub> = 3.0 Vdc) BD675G, BD677G, BD679G, BD681G (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 3.0 Vdc) BD675AG, BD677AG, BD679AG	h <sub>FE</sub>	750 750	- -	-
Collector–Emitter Saturation Voltage, (Note 1) ( $I_C = 1.5$ Adc, $I_B = 30$ mAdc) BD677G, BD679G, BD681G ( $I_C = 2.0$ Adc, $I_B = 40$ mAdc) BD675AG, BD677AG, BD679AG	V <sub>CE(sat)</sub>	-	2.5 2.8	Vdc
Base-Emitter On Voltage, (Note 1) (I <sub>C</sub> = 1.5 Adc, V <sub>CE</sub> = 3.0 Vdc) BD677G, BD679G, BD681G (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 3 0 Vdc) BD675AG, BD677AG, BD679AG	V <sub>BE(on)</sub>	-	2.5 2.5	Vdc
DYNAMIC CHARACTERISTICS				
Small Signal Current Gain (I <sub>C</sub> = 1.5 Adc, V <sub>CE</sub> = 3.0 Vdc, f = 1.0 MHz)	h <sub>fe</sub>	1.0	_	_

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width  $\leq 300 \, \mu s$ , Duty Cycle  $\leq 2.0\%$ .

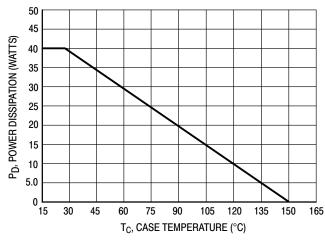


Figure 1. Power Temperature Derating

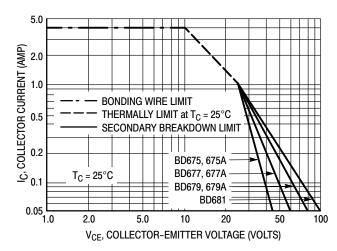


Figure 2. DC Safe Operating Area

# BD675G, BD675AG, BD677G, BD677AG, BD679G, BD679AG, BD681G

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

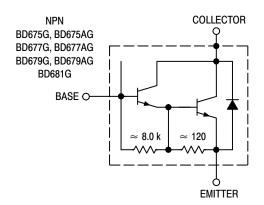


Figure 3. Darlington Circuit Schematic

### **ORDERING INFORMATION**

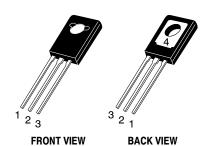
Device	Package	Shipping
BD681G	TO-225 (Pb-Free)	500 Units / Box

## **DISCONTINUED** (Note 2)

BD675G	TO-225 (Pb-Free)	500 Units / Box
BD675AG	TO-225 (Pb-Free)	500 Units / Box
BD677G	TO-225 (Pb-Free)	500 Units / Box
BD677AG	TO-225 (Pb-Free)	500 Units / Box
BD679G	TO-225 (Pb-Free)	500 Units / Box
BD679AG	TO-225 (Pb-Free)	500 Units / Box

DISCONTINUED: These devices are not recommended for new design. Please contact your onsemi representative for information. The
most current information on these devices may be available on <a href="https://www.onsemi.com">www.onsemi.com</a>.

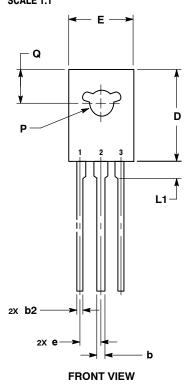


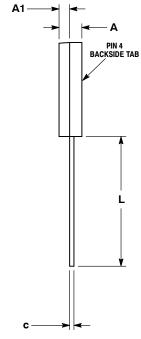


TO-225 CASE 77-09 **ISSUE AD** 

**DATE 25 MAR 2015** 

# SCALE 1:1



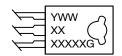


**SIDE VIEW** 

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.40	3.00		
A1	1.00	1.50		
b	0.60	0.90		
b2	0.51	0.88		
С	0.39	0.63		
D	10.60	11.10		
E	7.40	7.80		
е	2.04	2.54		
L	14.50	16.63		
L1	1.27	2.54		
P	2.90	3.30		
Q	3.80	4.20		

## **GENERIC MARKING DIAGRAM\***



= Year ww

= Work Week XXXXX = Device Code = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

,	EMITTER COLLECTOR	2., 4.	CATHODE ANODE		COLLECTOR	2., 4.	ANODE 1 ANODE 2		MT 2
STYLE 6:	BASE	STYLE 7:	GATE	3. STYLE 8:	EMITTER	STYLE 9:	GATE	3. STYLE 10:	GATE
	CATHODE	PIN 1.			SOURCE	PIN 1.			SOURCE
	GATE ANODE	,	GATE MT 2		GATE DRAIN	2., 4.	DRAIN	,	DRAIN GATE

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DESCRIPTION:	TO-225		PAGE 1 OF 1		

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